

## **Method For Forming Contact window**

### **ABSTRACT OF THE INVENTION**

5 A method for forming contact window is disclosed. Essential concept of the invention comprises over coating layer formed over surface before forming contact window is formed and the etching rate of over coating layer is higher than etching rate of underlying layer. The method comprises following steps: First, forming semiconductor structures on  
10 surface of wafer. Second, forming a coating layer over the surface and covering these semiconductor structures. Third, forming an over coating layer on the coating layer, where etching rate of over coating layer is higher than etching rate of coating layer. Finally, form contact window with outwardly winded shape. Thus, contact window formed by the  
15 invention is more convenient for filling material than contact window formed by conventional method. In addition, because width of contact window is not obviously increased, this invention is more beneficial for deep-submicron fabrication.